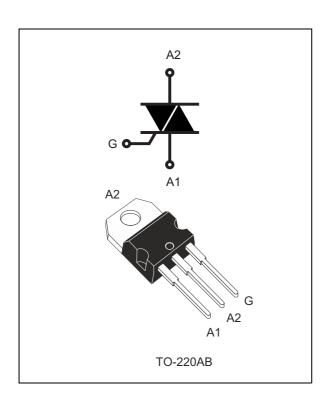


16 A logic level Triac

Datasheet - production data



Description

Available in through-hole package, the T1610T-8T Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller due to its 10 mA gate current requirement.

Table 1. Device summary

Symbol	Value	Unit
I _{T(rms)}	16	А
V_{DRM}, V_{RRM}	800	V
V_{DSM}, V_{RSM}	900	V
I _{GT}	10	mA

Features

- Medium current Triac
- Three quadrants
- ECOPACK®2 compliant component

Applications

- · General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

Characteristics T1610T-8T

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Table 2. Absolute ratings (limiting values, $T_j = 25$ °C unless otherwise stated)

Symbol	Paramete	Value	Unit		
I _{T(rms)}	On-state rms current (full sine wave	T _C = 129 °C	16	Α	
l	Non repetitive surge peak on-state	f = 50 Hz	t = 20 ms	120	А
I _{TSM}	current (full cycle, T_j initial = 25 °C)	f = 60 Hz	t = 16.7 ms	126	^
l ² t	I ² t value for fusing, T _j initial = 25 °C		$t_p = 10 \text{ ms}$	95	A ² s
V _{DRM} ,	Repetitive surge peak off-state volta	ige	T _j = 150 °C	600	V
V_{RRM}	Nepetitive surge peak oil-state voita	T _j = 125 °C	800	V	
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state v	t _p = 10 ms	900	٧	
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \le 100 \text{ ns}$	F = 100 Hz	100	A/µs	
I _{GM}	Peak gate current $t_p = 20 \mu s$		T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation $T_j = 150 ^{\circ}\text{C}$			1	W
T _{stg}	Storage junction temperature range			- 40 to + 150	°C
Tj	Operating junction temperature range			- 40 to + 150	
T_L	Maximum lead temperature for sold	260	°C		

Table 3. Electrical characteristics ($T_i = 25$ °C, unless otherwise specified)

Symbol	Test conditions	Quadrant		Value	Unit
	$V_D = 12 \text{ V}, R_1 = 30 \Omega$	1 - 11 - 111	Min.	0.5	m A
I _{GT}	VD = 12 V, IXL = 30 \$2	1 - 11 - 111	Max.	10	mA mA
V _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	1.3	V
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 125 \text{ °C}$	1 - 11 - 111	Min.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA		Max.	15	mA
	I _G = 1.2 I _{GT}	1 - 111	Max.	20	- mA
I _L		II		25	
dV/dt ⁽¹⁾	$V_D = V_R = 536 \text{ V}$, gate open	T _j = 125 °C	Min.	250	V/µs
u v/ui、	$V_D = V_R = 402 \text{ V, gate open}$	T _j = 150 °C	IVIIII.	170	V/µs
(dl/dt)c ⁽¹⁾	(dV/dt)c = 0.1 V/μs	T _j = 125 °C	- Min.	21.6	A/ms
(di/di)C		T _j = 150 °C		15.1	
(dl/dt)c ⁽¹⁾	(-1)//-14) - 40.1//	T _j = 125 °C	Min.	11.3	- A/ms
(ui/ut)c· /	$(dV/dt)c = 10 V/\mu s$	T _j = 150 °C	ivilli.	5	

^{1.} For both polarities of A2 referenced to A1

T1610T-8T Characteristics

Table	4	Static c	harac	teristics
Iabic	╼.	Juane C	, i i a i a c	เซาเอเเบอ

Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	I _{TM} = 22.6 A, t _p = 380 μs	T _j = 25 °C	Max.	1.55	V
V _{t0} (1)	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	Max.	27	mΩ
	V - V - 800 V	T _j = 25 °C	Max.	7.5	μΑ
I _{DRM} I _{RRM}	$V_{DRM} = V_{RRM} = 800 \text{ V}$	T _j = 125 °C	iviax.	1	mA
'KKIVI	V _{DRM} = V _{RRM} = 600 V	T _j = 150 °C	Max.	3	IIIA

^{1.} For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	1.1	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus on-state rms current

Figure 2. On-state rms current versus case temperature

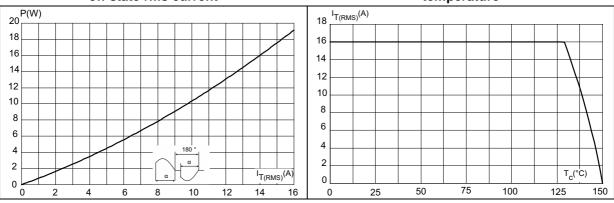
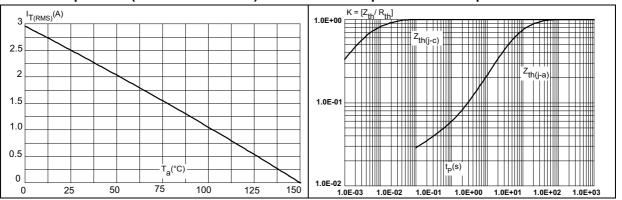


Figure 3. On-state rms current versus ambient temperature (free air convection)

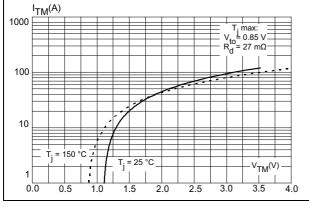
Figure 4. Relative variation of thermal impedance versus pulse duration



T1610T-8T **Characteristics**

Figure 5. On-state characteristics (maximum values)

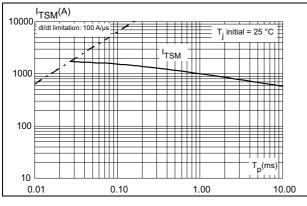
Figure 6. Surge peak on-state current versus number of cycles I_{TSM}(A) 130 120 Non repetitive T_i initial = 25 110 100 90 80



70 60 50 40 Repetitive $T_c = 129 \, ^{\circ}C$ 30 20 10 Number of cycles 1000

Figure 7. Non repetitive surge peak on-state current

Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



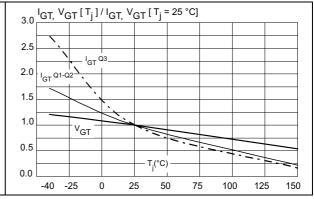
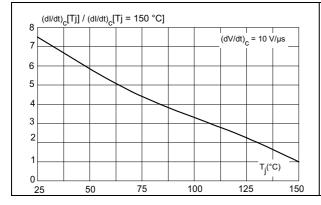
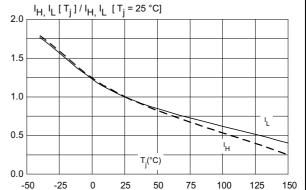


Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)

Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)





T1610T-8T Characteristics

Figure 11. Relative variation of critical rate of decrease of main current (dl/dt)_C versus reapplied (dV/dt)_C (maximum values)

Figure 12. Relative variation of static dV/dt immunity versus junction temperature (typical values)

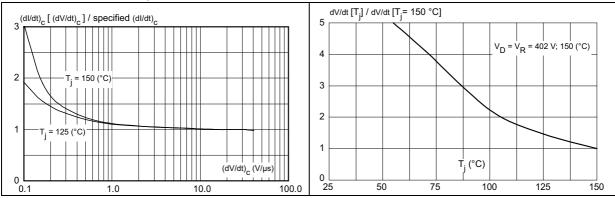
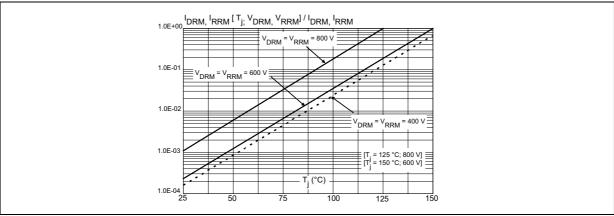


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information T1610T-8T

2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 14. TO-220AB dimension definitions Ε $\emptyset P$ Resin gate 0.5 mm max. protrusion⁽¹⁾ Q H1 D **D1** L30 **L20** J1 L1 b1 b Resin gate C 0.5 mm max. protrusion⁽¹⁾ (1) Resin gate position accepted in each of the two position shown as well as the symmetrical opposites

T1610T-8T Package information

Table 6. TO-220AB dimension values

	Dimensions				
Ref.	Millim	neters	Inch	nes	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.17	0.18	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.027	
D	15.25	15.75	0.60	0.62	
D1	1.27	typ.	0.05	typ.	
E	10	10.40	0.39	0.41	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.19	0.20	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.24	0.26	
J1	2.40	2.72	0.094	0.107	
L	13	14	0.51	0.55	
L1	3.50	3.93	0.137	0.154	
L20	16.40 typ.		0.64 typ.		
L30	28.90 typ.		1.13	typ.	
ØP	3.75	3.85	0.147	0.151	
Q	2.65	2.95 0.104		0.116	

Ordering information T1610T-8T

3 Ordering information

Figure 15. Ordering information scheme

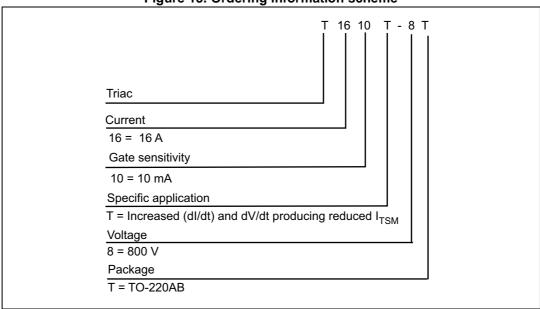


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1610T-8T	T1610T-8T	TO-220AB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
23-Oct-2014	1	Initial release.

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